

IN THE CLAIMS:

Claim 1. (Original) A semiconductor device characterized in that an interface layer, a diffusion suppressing layer and a high dielectric constant insulating film are sequentially formed in this order on one surface of a silicon substrate.

Claim 2. (Currently Amended) A semiconductor device as elianed in claim 1, therein
wherein the interface layer have an equivalently converted SiO₂ thickness of 1.0 nm or smaller.

Claim 3. (Currently Amended) A semiconductor device as elianed in claim 1 or 2, therein
wherein the constitutional element of the high dielectric constant insulating film is made the same as part of the constitutional elements of the interface layer.

Claim 4. (Original) A method for manufacturing a semiconductor device characterized by comprising: forming an initial layer on one surface of a silicon substrate; forming a diffusion suppressing layer on the surface of the initial layer; performing heat treatment to allow the initial layer to become an interface layer mutually diffused with the silicon substrate; and forming a high dielectric constant insulating film on the surface of the diffusion suppressing layer.

Claim 5. (Original) A method for manufacturing a semiconductor device characterized by comprising: forming an initial layer on one surface of a silicon substrate; forming a diffusion suppressing layer on the surface of the initial layer; forming a high dielectric constant insulating film on the surface of the diffusion suppressing layer; and performing heat treatment to allow the initial layer to become an interface layer mutually diffused with the silicon substrate.

Claim 6. (New) A semiconductor device as in claim 2, wherein the constitutional element of the high dielectric constant insulating film is made the same as part of the constitutional elements of the interface layer.